

<b>INFORMATION DISCLOSURE CITATION</b>  <b>PTO-1449</b>		<b>Atty. Docket No.</b> NTI-023-1D		<b>Serial No.</b> Filed Herewith		
		<b>Applicant</b> LIU, Yong				
		<b>Filing Date</b> Filed Herewith		<b>Group</b>		
<b>U.S. PATENT DOCUMENTS</b>						
<b>EXAMINER'S INITIALS</b>	<b>PATENT NO.</b>	<b>DATE</b>	<b>NAME</b>	<b>CLASS</b>	<b>SUBCLASS</b>	<b>FILING DATE</b>
<i>EC</i>	4,231,811	11/4/1980	Somekh, et al.	148	1.5	9/13/1979
	4,426,584	1/17/1984	Bohlen, et al.	250	492.2	6/3/1981
	4,456,371	6/26/1984	Lin	355	71	6/30/1982
	4,812,962	3/14/1989	Witt	364	490	4/9/1987
	4,895,780	1/23/1990	Nissan-Cohen, et al.	430	5	10/25/1988
	4,902,899	2/20/1990	Lin, et al.	250	492.1	6/1/1987
	5,051,598	9/24/1991	Ashton, et al.	250	492.2	9/12/1990
	5,182,718	1/26/1993	Harafuji, et al.	364	490	3/29/1990
	5,208,124	5/4/1993	Sporon-Fiedler, et al.	430	5	3/19/1991
	5,241,185	8/31/1993	Meiri, et al.	250	492.2	1/8/1992
	5,242,770	9/7/1993	Chen, et al.	430	5	1/16/1992
	5,256,505	10/26/1993	Chen, et al.	430	5	8/21/1992
	5,326,659	7/5/1994	Liu, et al.	430	5	3/5/1992
	5,340,700	8/23/1994	Chen, et al.	430	312	11/3/1993
	5,432,714	7/11/1995	Chung, et al.	364	525	9/2/1994
	5,447,810	9/5/1995	Chen, et al.	430	5	2/9/1994
	5,498,579	3/12/1996	Borodovsky, et al.	437	250	6/8/1994
	5,553,273	9/3/1996	Liebmann	395	500	4/17/1995
	5,553,274	9/3/1996	Liebmann	395	500	6/6/1995
	5,572,598	11/5/1996	Wihl, et al.	382	144	2/25/1994
	5,631,110	5/20/1997	Shioiri, et al.	430	5	6/5/1995
	5,636,002	6/3/1997	Garofalo	355	53	10/31/1995
<i>EC</i>	5,657,235	8/12/1997	Liebmann, et al.	364	474.24	5/3/1995

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*R. Porosco*

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EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
<i>DL</i>	5,663,017	9/2/1997	Schinella, et al.	430	5	6/7/1995
	5,663,893	9/2/1997	Wampler, et al.	364	491	5/3/1995
	5,682,323	10/28/1997	Pasch, et al.	364	491	3/6/1995
	5,705,301	1/6/1998	Garza, et al.	430	5	2/27/1996
	5,707,765	1/13/1998	Chen	430	5	5/28/1996
	5,723,233	3/3/1998	Garza, et al.	430	5	2/27/1996
	5,740,068	4/14/1998	Liebmann, et al.	364	489	5/30/1996
	5,766,806	6/16/1998	Spence	430	5	9/9/1996
	5,795,688	8/18/1998	Burdorf, et al.	430	30	8/14/1996
	5,801,954	9/1/1998	Le, et al.	364	488	4/24/1996
	5,804,340	9/8/1998	Garza, et al.	430	5	12/23/1996
	5,815,685	9/29/1998	Kamon	395	500	9/15/1995
	5,821,014	10/13/1998	Chen, et al.	430	5	2/28/1997
	5,825,647	10/20/1998	Tsudaka	364	167.03	3/12/1996
	5,827,623	10/27/1998	Ishida, et al.	430	5	10/30/1996
	5,847,959	12/8/1998	Veneklasen, et al.	364	468.28	1/28/1997
	5,862,058	1/19/1999	Samuels, et al.	364	491	5/16/1996
	5,863,682	1/26/1999	Abe, et al.	430	30	2/21/1997
	5,879,844	3/9/1999	Yamamoto, et al.	430	30	12/20/1996
	5,885,734	3/23/1999	Pierrat, et al.	430	5	8/15/1996
	5,900,338	5/4/1999	Garza, et al.	430	5	8/15/1997
	5,958,635	9/28/1999	Reich, et al.	430	30	10/20/1997
<i>DL</i>	5,972,541	10/26/1999	Sugasawara, et al.	430	5	3/4/1998

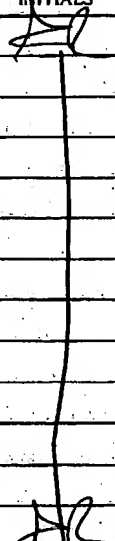
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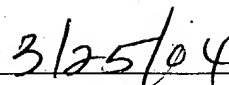
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	5,994,002	11/30/1999	Matsuoka	430	5	9/4/1997
	6,007,310	12/28/1999	Jacobsen, et al.	417	362	5/23/1997
	6,009,250	12/28/1999	Ho, et al.	395	500.06	9/30/1997
	6,009,251	12/28/1999	Ho, et al.	395	500.06	9/30/1997
	6,011,911	1/4/2000	Ho, et al.	395	500.06	9/30/1997
	6,077,310	6/20/2000	Yamamoto, et al.	716	19	1/29/1999
	6,078,738	6/20/2000	Garza, et al.	395	500.22	5/8/1997
	6,081,658	6/27/2000	Rieger, et al.	395	500.22	12/31/1997
	6,081,659	6/27/2000	Garza, et al.	395	500.22	4/26/1999
	6,114,071	9/5/2000	Chen, et al.	430	5	4/6/1998
	6,289,499	9/11/2001	Rieger, et al.	716	21	1/7/2000
	6,171,731 B1	1/9/2001	Medvedeva, et al.	430	5	1/20/1999
	6,249,597 B1	6/19/2001	Tsudaka	382	144	12/17/1998

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EC	5,282,140	1/25/1994	Tazawa, et al.	364	468	6/24/1992
	6,014,456	1/11/2000	Tsudaka	382	144	7/15/1996
	6,154,563	11/28/2000	Tsudaka	382	144	12/17/1998
	6,225,025 B1	5/1/2001	Hoshino	430	296	9/22/1998
	6,298,473 B1	10/2/2001	Ono, et al.	716	21	12/3/1998
	6,339,836 B1	1/15/2002	Eisenhofer, et al.	716	5	8/24/1998
	6,453,457 B1	9/17/2002	Pierrat, et al.	716	19	9/29/2000
AB2	2002/0076622 A1	6/20/2002	Pierrat, et al.	430	5	12/20/2000
	2002/0100004 A1	7/25/2002	Pierrat, et al.	716	5	3/15/2002

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*A. Duaso*

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<i>JS</i>	5,991,006	11/23/0199	Tsudaka	355	53	10/27/1997
	6,016,357	1/18/2000	Neary, et al.	382	144	6/16/1997
	6,091,845	7/18/2000	Pierrat, et al.	382	144	2/24/1998
	6,272,236	8/7/2001	Pierrat, et al.	382	144	7/18/2000
	6,243,855 B1	6/5/2001	Kobayashi, et al.	716	19	9/29/1998
	2002/0019729 A1	2/14/2002	Chang, et al.	703	6	8/7/1998
<i>JS</i>	2002/0035461 A1	3/21/2002	Chang, et al.	703	13	7/16/2001
<i>JS</i>	6,183,916	2/06/2001	Kuo et al.	430	5	9/13/1999
<i>JS</i>	6,425,117	7/23/2002	Pasch et al.	716	21	9/29/1997

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*J. Proasce*

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<b>FOREIGN PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
AP	WO 00/36525 A2	6/22/2000	WO			<input type="checkbox"/>	<input type="checkbox"/>
	3-80525	4/5/1991	JP			<input type="checkbox"/>	<input type="checkbox"/>
	WO 00/67074 A1	11/9/2000	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 00/67075 A1	11/9/2000	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 00/67076 A1	11/9/2000	WO			<input type="checkbox"/>	<input type="checkbox"/>
	2,324,169 A	10/14/1998	GB			<input type="checkbox"/>	<input type="checkbox"/>
	3-210560	9/13/1991	JP			<input type="checkbox"/>	<input type="checkbox"/>
	8-236317	9/6/1996	JP			<input type="checkbox"/>	<input type="checkbox"/>
	WO 99/47981	9/23/1999	WO			<input type="checkbox"/>	<input type="checkbox"/>
	10-133356	5/22/1998	JP			<input type="checkbox"/>	<input type="checkbox"/>
AP	11-143085	5/28/1999	JP			<input type="checkbox"/>	<input type="checkbox"/>

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A. Rosasco

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EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
<i>[Signature]</i>	WO 99/14706 A2/A3	3/25/1999	WO			<input type="checkbox"/>	<input type="checkbox"/>

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*[Signature]*

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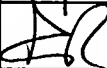
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<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>			
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	Kang, D., et al., "Effects of Mask Bias on the Mask Error Enhancement Factor (MEEF) of Contact Holes" (11 pages).		
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	Mathur, B.P., et al., "Quantitative Evaluation of Shape of Image on Photoresist of Square Apertures", IEEE, Transactions On Electron Devices, Vol. 35, No. 3, pp. 294-297, March 1988.		
	Lin, B.J., "Methods to Print Optical Images at Low-k1 Factors", SPIE, Optical/Laser Microlithography III, Vol. 1264, pp. 2-13 (1990).		

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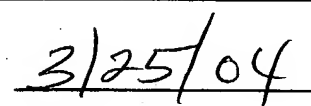
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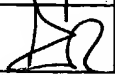
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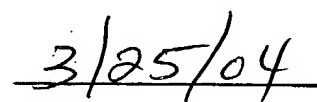
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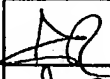
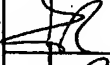


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		NTI-023-1D	Filed Herewith
		<b>Applicant</b>	
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<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>			
<b>EXAMINER'S INITIALS</b>	<b>CITATION</b>		
	Spence, C., et al., "Integration of Optical Proximity Correction Strategies in Strong Phase Shifters Design for Poly-Gate Layers", Bacus News, Vol. 15, Issue 12, pp. 1, 4-13, December 1999.		
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<i>[Signature]</i>	Cobb, N., et al., "Fast, Low-Complexity Mask Design", SPIE, Vol. 2440, pp. 313-327, February 22-24, 1995.		
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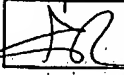
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